

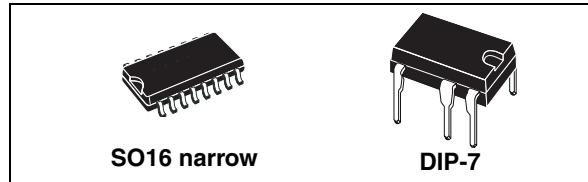
## Fixed frequency VIPer™ plus family

### Features

- 800 V avalanche rugged power section
- PWM operation with frequency jittering for low EMI
- Operating frequency:
  - 60 kHz for L type
  - 115 kHz for H type
- No need of auxiliary winding for low power application
- Standby power < 50 mW at 265 V<sub>AC</sub>
- Limiting current with adjustable set point
- On-board soft-start
- Safe auto-restart after a fault condition
- Hysteretic thermal shutdown

### Application

- Replacement of capacitive power supply
- Auxiliary power supply for appliances,
- Power metering
- LED drivers

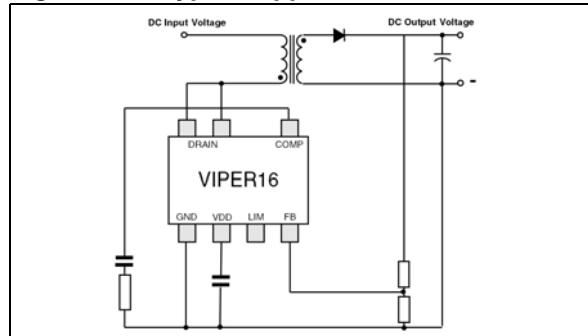


### Description

The device is an off-line converter with an 800 V avalanche ruggedness power section, a PWM controller, user defined overcurrent limit, protection against feedback network disconnection, hysteretic thermal protection, soft start up and safe auto restart after any fault condition. It is able to power itself directly from the rectified mains, eliminating the need for an auxiliary bias winding.

Advance frequency jittering reduces EMI filter cost. Burst mode operation and the devices very low consumption both help to meet the standard set by energy saving regulations.

**Figure 1. Typical application**



**Table 1. Device summary**

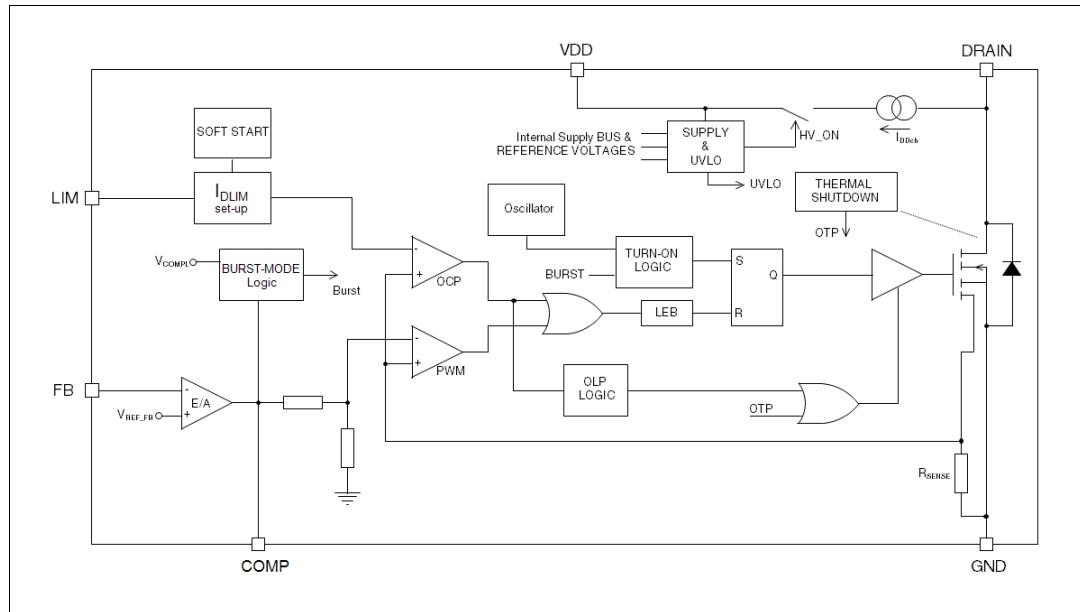
Order codes	Package	Packaging
VIPER16LN	DIP-7	Tube
VIPER16HN		Tube
VIPER16HD	SO16 narrow	Tube
VIPER16HDTR		Tape and reel
VIPER16LD		Tube
VIPER16LDTR		Tape and reel

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# 1 Block diagram

Figure 2. Block diagram



# 2 Typical power

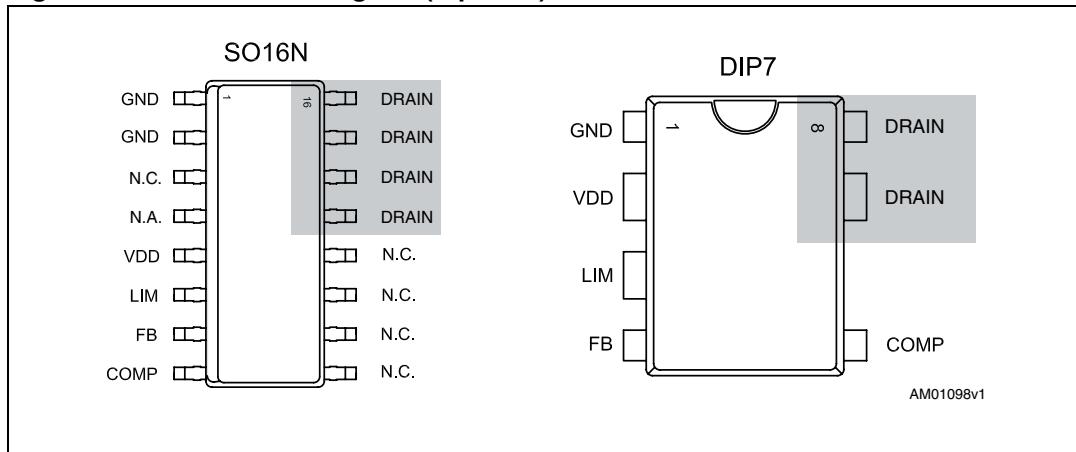
Table 2. Typical power

Part number	230 V <sub>AC</sub>		85-265 V <sub>AC</sub>	
	Adapter <sup>(1)</sup>	Open frame <sup>(2)</sup>	Adapter <sup>(1)</sup>	Open frame <sup>(2)</sup>
VIPER16	9 W	10 W	5 W	6 W

1. Typical continuous power in non ventilated enclosed adapter measured at 50 °C ambient.
2. Maximum practical continuous power in an open frame design at 50 °C ambient, with adequate heat sinking.

### 3 Pin settings

Figure 3. Connection diagram (top view)



Note:

The copper area for heat dissipation has to be designed under the DRAIN pins.

Table 3. Pin description

Pin N.		Name	Function
DIP-7	SO16		
1	1-2	GND	Connected to the source of the internal power MOSFET and controller ground reference.
-	4	N.A.	Not available for user. It can be connected to GND (pins 1-2) or left not connected.
2	5	VDD	Supply voltage of the control section. This pin provides the charging current of the external capacitor.
3	6	LIM	This pin allows setting the drain current limitation. The limit can be reduced by connecting an external resistor between this pin and GND. Pin left open if default drain current limitation is used.
4	7	FB	Inverting input of the internal trans conductance error amplifier. Connecting the converter output to this pin through a single resistor results in an output voltage equal to the error amplifier reference voltage (See $V_{FB\_REF}$ on <a href="#">Table 7</a> ). An external resistors divider is required for higher output voltages.
5	8	COMP	Output of the internal trans conductance error amplifier. The compensation network have to be placed between this pin and GND to achieve stability and good dynamic performance of the voltage control loop. The pin is used also to directly control the PWM with an optocoupler. The linear voltage range extends from $V_{COMPL}$ to $V_{COMPH}$ ( <a href="#">Table 7</a> ).
7,8	13-16	DRAIN	High voltage drain pin. The built-in high voltage switched start-up bias current is drawn from this pin too. Pins connected to the metal frame to facilitate heat dissipation.

## 4 Electrical data

### 4.1 Maximum ratings

**Table 4. Absolute maximum ratings**

Symbol	Pin (DIP-7)	Parameter	Value		Unit
			Min	Max	
$V_{DRAIN}$	7, 8	Drain-to-source (ground) voltage		800	V
$E_{AV}$	7, 8	Repetitive avalanche energy (limited by $T_J = 150^\circ\text{C}$ )		2	mJ
$I_{AR}$	7, 8	Repetitive avalanche current (limited by $T_J = 150^\circ\text{C}$ )		1	A
$I_{DRAIN}$	7, 8	Pulse drain current (limited by $T_J = 150^\circ\text{C}$ )		2.5	A
$V_{COMP}$	5	Input pin voltage	-0.3	3.5	V
$V_{FB}$	4	Input pin voltage	-0.3	4.8	V
$V_{LIM}$	3	Input pin voltage	-0.3	2.4	V
$V_{DD}$	2	Supply voltage	-0.3	Self limited	V
$I_{DD}$	2	Input current		20	mA
$P_{TOT}$		Power dissipation at $T_A < 40^\circ\text{C}$ (DIP-7)		1	W
		Power dissipation at $T_A < 60^\circ\text{C}$ (SO16N)		1	W
$T_J$		Operating junction temperature range	-40	150	°C
$T_{STG}$		Storage temperature	-55	150	°C

### 4.2 Thermal data

**Table 5. Thermal data**

Symbol	Parameter	Max value SO16N	Max value DIP-7	Unit
$R_{thJP}$	Thermal resistance junction pin (Dissipated power = 1 W)	35	40	°C/W
$R_{thJA}$	Thermal resistance junction ambient (Dissipated power = 1 W)	90	110	°C/W
$R_{thJA}$	Thermal resistance junction ambient <sup>(1)</sup> (Dissipated power = 1 W)	80	90	°C/W

1. When mounted on a standard single side FR4 board with 100 mm<sup>2</sup> (0.155 sq in) of Cu (35 µm thick)

## 4.3 Electrical characteristics

( $T_J = -25$  to  $125$  °C,  $V_{DD} = 14$  V <sup>(a)</sup>; unless otherwise specified)

**Table 6. Power section**

Symbol	Parameter	Test condition	Min	Typ	Max	Unit
$V_{BVDS}$	Break-down voltage	$I_{DRAIN} = 1$ mA, $V_{COMP} = GND$ , $T_J = 25$ °C	800			V
$I_{OFF}$	OFF state drain current	$V_{DRAIN} = \text{max rating}$ , $V_{COMP} = GND$			60	µA
$R_{DS(on)}$	Drain-source on state resistance	$I_{DRAIN} = 0.2$ A, $T_J = 25$ °C		20	24	Ω
		$I_{DRAIN} = 0.2$ A, $T_J = 125$ °C		40	48	Ω
$C_{oss}$	Effective (energy related) output capacitance	$V_{DRAIN} = 0$ to $640$ V		10		pF

**Table 7. Supply section**

Symbol	Parameter	Test condition	Min	Typ	Max	Unit
<b>Voltage</b>						
$V_{DRAIN\_START}$	Drain-source start voltage		40	50	60	V
$I_{DDch1}$	Start up charging current	$V_{DRAIN} = 100$ V to $640$ V, $V_{DD} = 4$ V	-0.6		-1.8	mA
$I_{DDch2}$	Charging current during operation	$V_{DRAIN} = 100$ V to $640$ V, $V_{DD} = 9$ V falling edge	-7		-13	mA
$V_{DD}$	Operating voltage range		11.5		23.5	V
$V_{DDclamp}$	$V_{DD}$ clamp voltage	$I_{DD} = 15$ mA	23.5			V
$V_{DDon}$	$V_{DD}$ start up threshold		12	13	14	V
$V_{DDCSon}$	VDD on internal high voltage current generator threshold		9.5	10.5	11.5	V
$V_{DDoff}$	$V_{DD}$ under voltage shutdown threshold		7	8	9	V
<b>Current</b>						
$I_{DD0}$	Operating supply current, not switching	$F_{OSC} = 0$ kHz, $V_{COMP} = GND$			0.6	mA
$I_{DD1}$	Operating supply current, switching	$V_{DRAIN} = 120$ V, $F_{SW} = 60$ kHz			1.3	mA
		$V_{DRAIN} = 120$ V, $F_{SW} = 115$ kHz			1.5	mA
$I_{DDoff}$	Operating supply current with $V_{DD} < V_{DDoff}$	$V_{DD} < V_{DDoff}$			0.35	mA
$I_{DDol}$	Open loop failure current threshold	$V_{DD} = V_{DDclamp}$ $V_{COMP} = 3.3$ V	4			mA

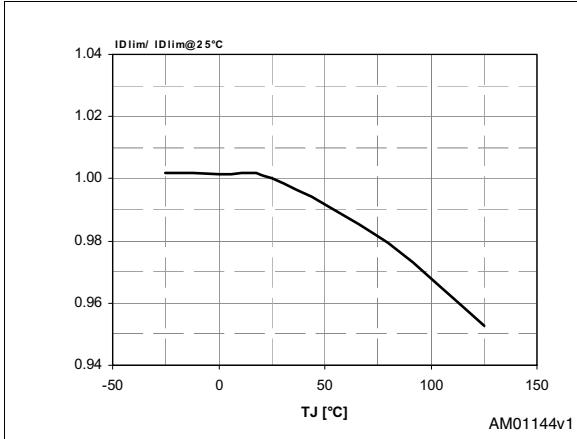
a. Adjust  $V_{DD}$  above  $V_{DDon}$  start-up threshold before setting to 14 V

**Table 8. Controller section**

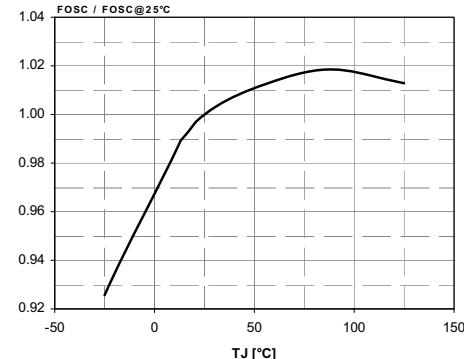
Symbol	Parameter	Test condition	Min	Typ	Max	Unit
<b>Error amplifier</b>						
$V_{REF\_FB}$	FB reference voltage		3.2	3.3	3.4	V
$I_{FB\_PULL\ UP}$	Current pull up			-1		$\mu A$
$G_M$	Trans conductance			2		$mA/V$
<b>Current setting (LIM) pin</b>						
$V_{LIM\_LOW}$	Low level clamp voltage	$I_{LIM} = -100 \mu A$		0.5		V
<b>Compensation (COMP) pin</b>						
$V_{COMPH}$	Upper saturation limit	$T_J = 25^\circ C$		3		V
$V_{COMPL}$	Burst mode threshold	$T_J = 25^\circ C$	1	1.1	1.2	V
$V_{COMPL\_HYS}$	Burst mode hysteresis	$T_J = 25^\circ C$		40		$mV$
$H_{COMP}$	$\Delta V_{COMP} / \Delta I_{DRAIN}$		4		9	$V/A$
$R_{COMP(DYN)}$	Dynamic resistance	$V_{FB} = GND$		15		$k\Omega$
$I_{COMP}$	Source / sink current	$V_{FB} > 100 mV$		150		$\mu A$
	Max source current	$V_{COMP} = GND, V_{FB} = GND$		220		$\mu A$
<b>Current limitation</b>						
$I_{Dlim}$	Drain current limitation	$I_{LIM} = -10 \mu A, V_{COMP} = 3.3 V, T_J = 25^\circ C$	0.38	0.4	0.42	A
$t_{SS}$	Soft-start time			8.5		ms
$T_{ON\_MIN}$	Minimum turn ON time				450	ns
$I_{Dlim\_bm}$	Burst mode current limitation	$V_{COMP} = V_{COMPL}$		85		mA
<b>Overload</b>						
$t_{OVL}$	Overload time			50		ms
$t_{RESTART}$	Restart time after fault			1		s
<b>Oscillator section</b>						
$F_{OSC}$	Switching frequency	$VIPer16L$	54	60	66	kHz
		$VIPer16H$	103	115	127	kHz
$F_D$	Modulation depth	$F_{OSC} = 60 \text{ kHz}$		$\pm 4$		kHz
		$F_{OSC} = 115 \text{ kHz}$		$\pm 8$		kHz
$F_M$	Modulation frequency			230		Hz
$D_{MAX}$	Maximum duty cycle		70		80	%
<b>Thermal shutdown</b>						
$T_{SD}$	Thermal shutdown temperature		150	160		$^\circ C$
$T_{HYST}$	Thermal shutdown hysteresis			30		$^\circ C$

## 5 Typical electrical characteristics

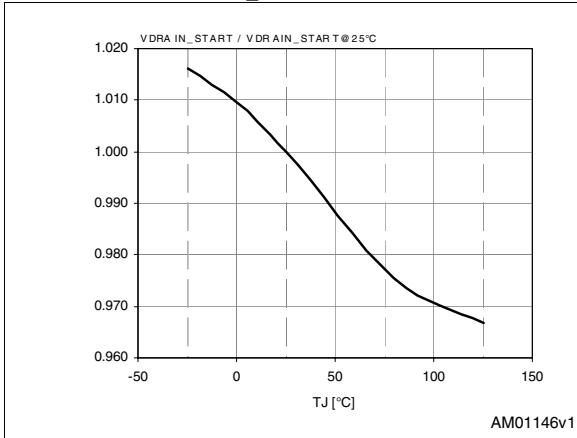
**Figure 4. IDlim vs TJ**



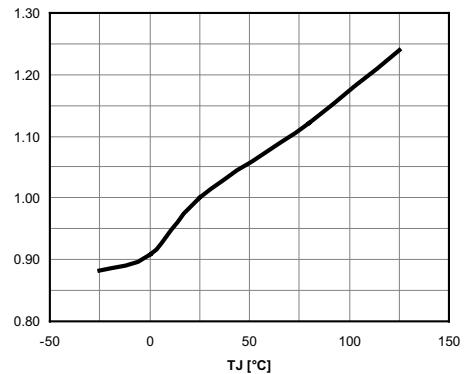
**Figure 5. Fosc vs TJ**



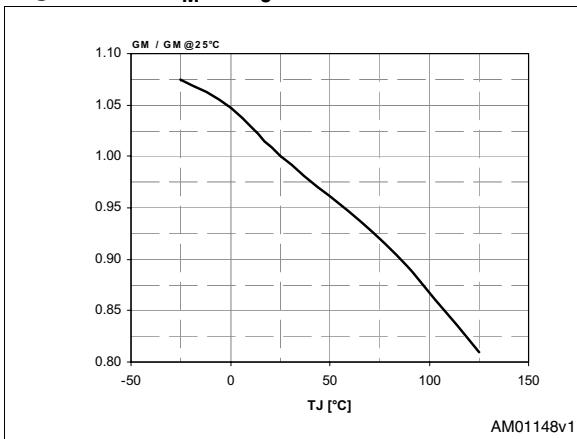
**Figure 6. V<sub>DRAIN\_START</sub> vs TJ**



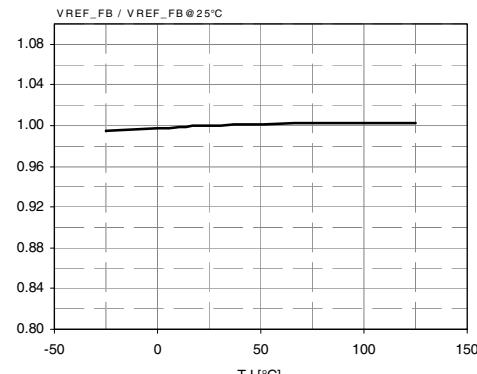
**Figure 7. H<sub>COMP</sub> vs TJ**

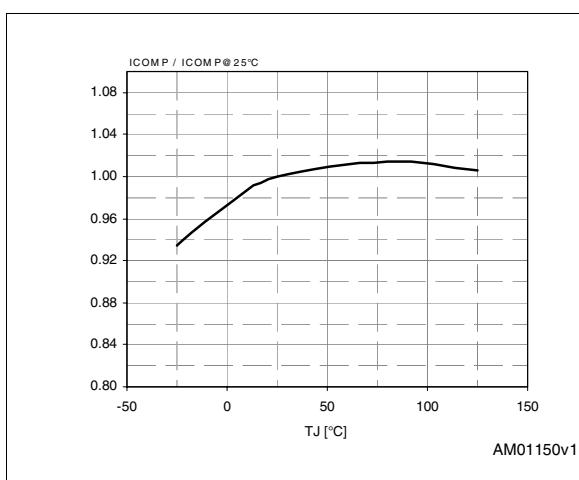
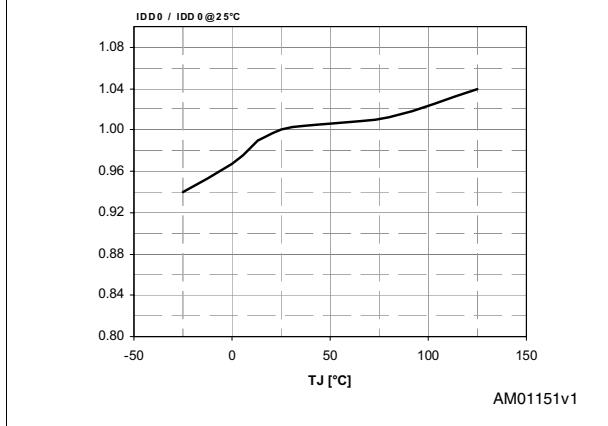
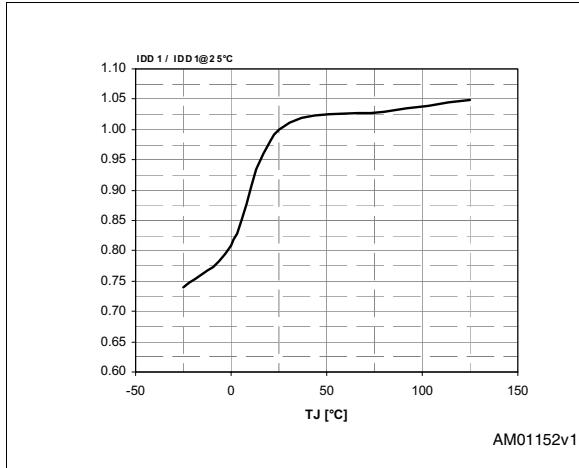
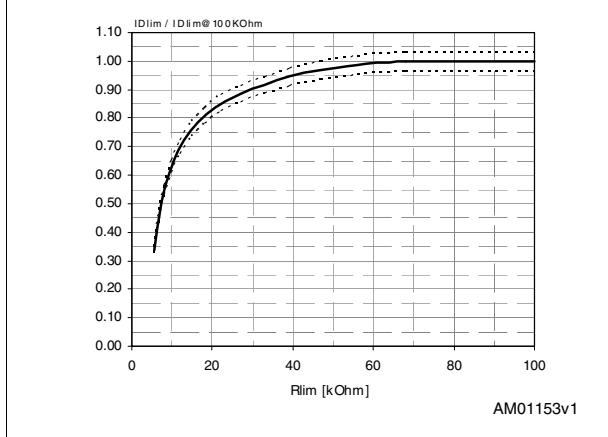
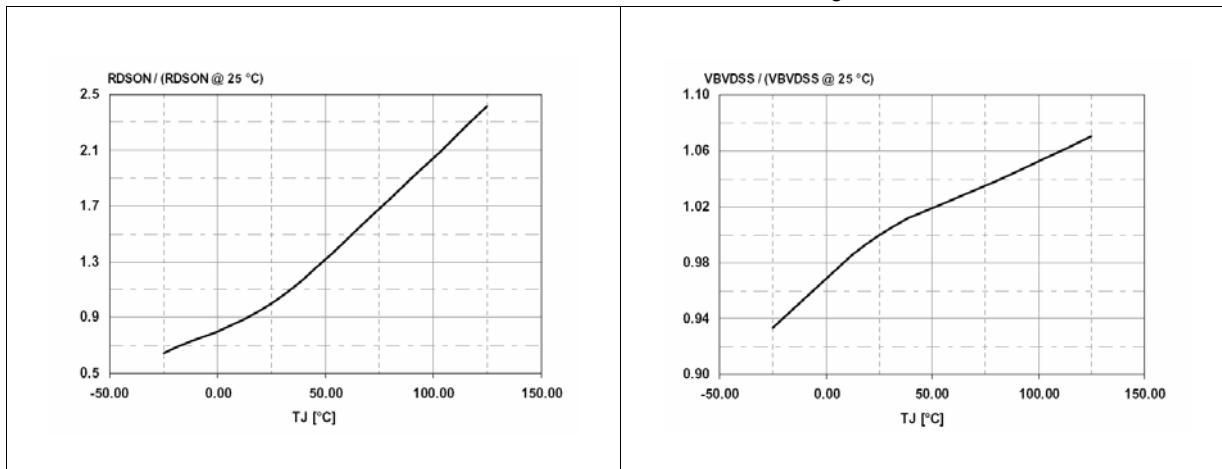


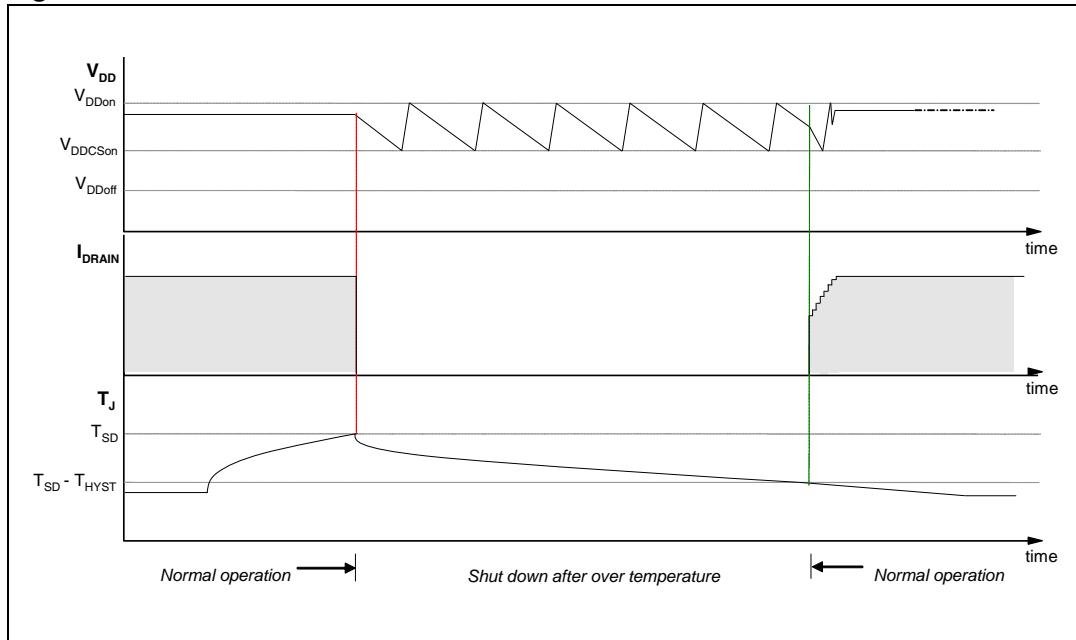
**Figure 8. G<sub>M</sub> vs TJ**



**Figure 9. V<sub>REF\_FB</sub> vs TJ**

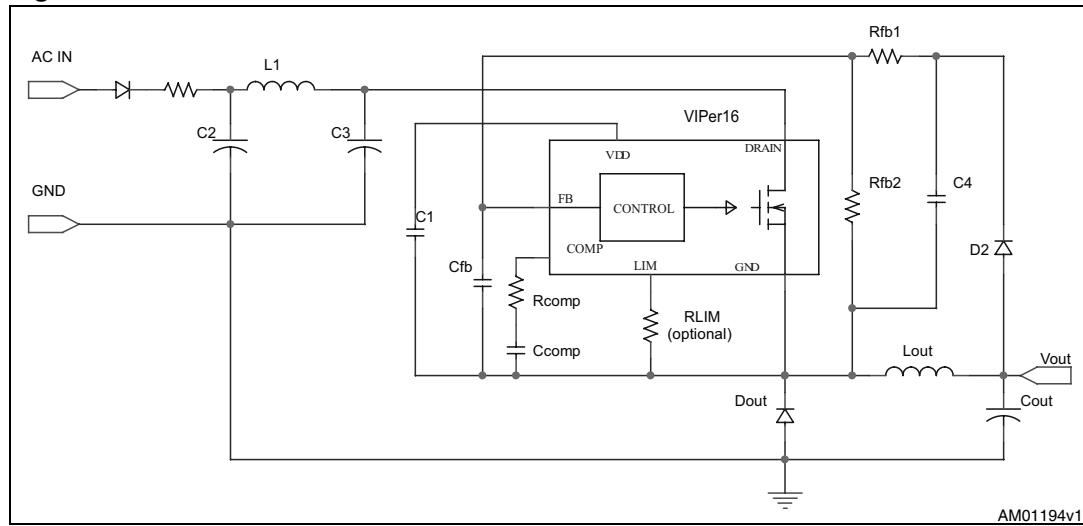


**Figure 10.  $I_{COMP}$  vs  $T_J$** **Figure 11. Operating supply current (no switching) vs  $T_J$** **Figure 12. Operating supply current (switching) vs  $T_J$** **Figure 13.  $ID_{lim}$  vs  $R_{LIM}$** **Figure 14. Power MOSFET on-resistance vs  $T_J$       Figure 15. Power MOSFET break down voltage vs  $T_J$** 

**Figure 16. Thermal shutdown**

## 6 Typical circuit

**Figure 17. Buck converter**



**Figure 18. Buck boost converter**

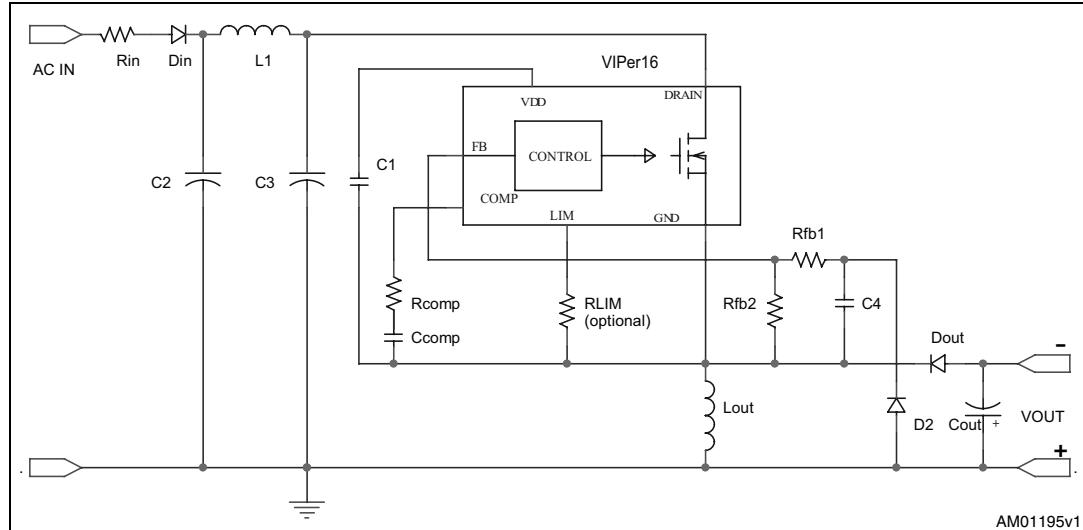


Figure 19. Flyback converter (primary regulation)

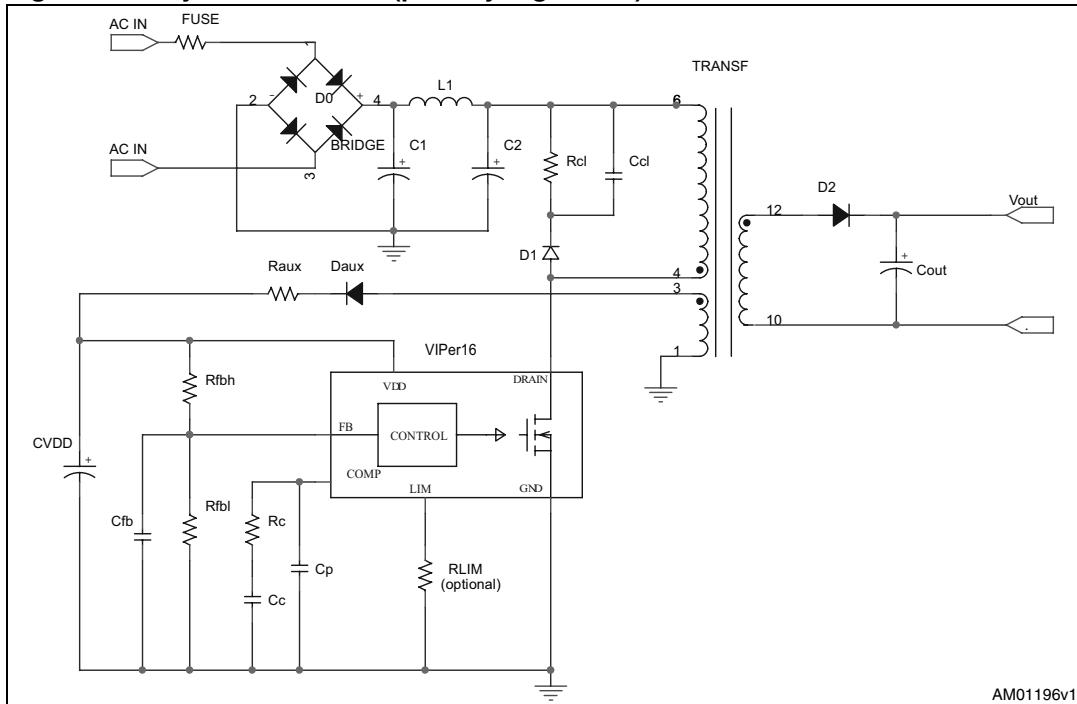
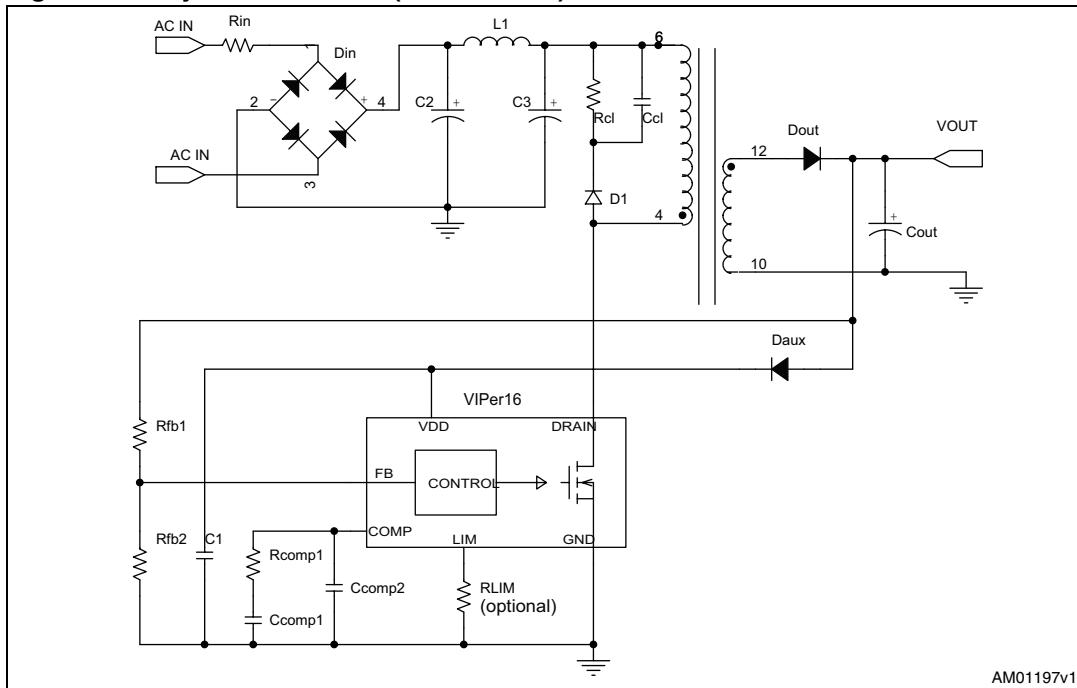


Figure 20. Flyback converter (non isolated)



## 7 Power section

The power section is implemented with an n-channel power MOSFET with a breakdown voltage of 800 V min. and a typical  $R_{DS(on)}$  of 20  $\Omega$ . It includes a SenseFET structure to allow a virtually lossless current sensing and the thermal sensor.

The gate driver of the power MOSFET is designed to supply a controlled gate current during both turn-ON and turn-OFF in order to minimize common mode EMI. During UVLO conditions, an internal pull-down circuit holds the gate low in order to ensure that the power MOSFET cannot be turned ON accidentally.

## 8 High voltage current generator

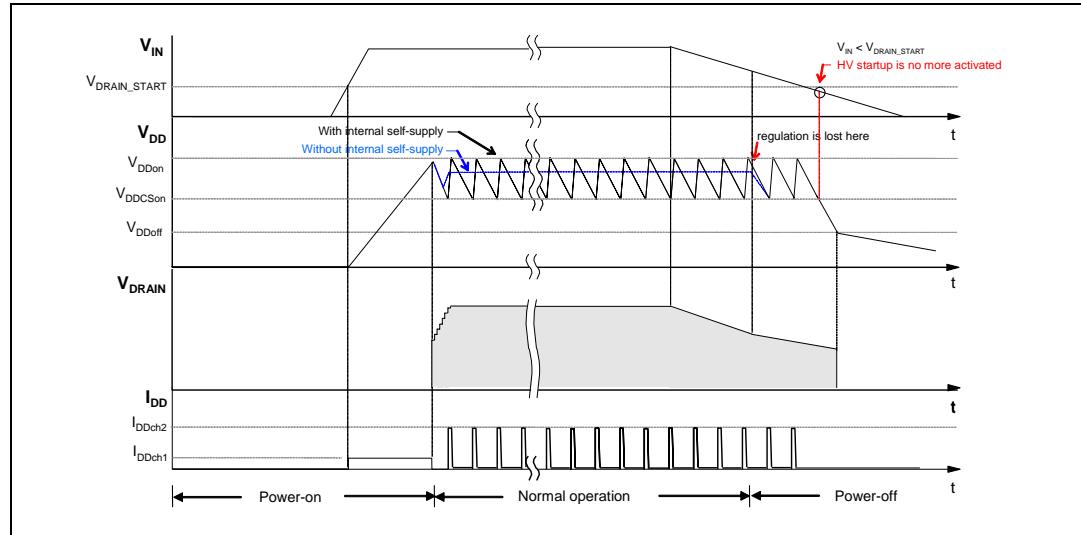
The high voltage current generator is supplied by the DRAIN pin. At the first start up of the converter it is enabled when the voltage across the input bulk capacitor reaches the  $V_{DRAIN\_START}$  threshold, sourcing a  $I_{DDch1}$  current (see [Table 7 on page 6](#)); as the  $V_{DD}$  voltage reaches the  $V_{DDon}$  threshold, the power section starts switching and the high voltage current generator is turned OFF. The VIPer16 is powered by the energy stored in the  $V_{DD}$  capacitor.

In steady state condition, if the self biasing function is used, the high voltage current generator is activated between  $V_{DDCSon}$  and  $V_{DDDon}$  (see [Table 7 on page 6](#)), delivering  $I_{DDch2}$ , see [Table 7 on page 6](#) to the  $V_{DD}$  capacitor during the MOSFET off time (see [Figure 21 on page 13](#)).

The device can also be supplied through the auxiliary winding; in this case the high voltage current source is disabled during steady-state operation, provided that VDD is above  $V_{DDCSon}$ .

At converter power-down, the  $V_{DD}$  voltage drops and the converter activity stops as it falls below  $V_{DDoff}$  threshold (see [Table 7 on page 6](#)).

**Figure 21. Power on and power off**



## 9 Oscillator

The switching frequency is internally fixed at 60 kHz (part number VIPER16LN or LD) or 115 kHz (part number VIPER16HN or HD).

In both cases the switching frequency is modulated by approximately  $\pm 4$  kHz (60 kHz version) or  $\pm 8$  kHz (115 kHz version) at 230 Hz (typical) rate, so that the resulting spread-spectrum action distributes the energy of each harmonic of the switching frequency over a number of sideband harmonics having the same energy on the whole but smaller amplitudes.

## 10 Soft start-up

During the converters' start-up phase, the soft-start function progressively increases the cycle-by-cycle drain current limit, up to the default value  $I_{Dlim}$ . By this way the drain current is further limited and the output voltage is progressively increased reducing the stress on the secondary diode. The soft-start time is internally fixed to  $t_{SS}$ , see typical value on [Table 8 on page 7](#), and the function is activated for any attempt of converter start-up and after a fault event.

This function helps prevent transformers' saturation during start-up and short-circuit.

## 11 Adjustable current limit set point

The VIPer16 includes a current mode PWM controller: cycle by cycle the drain current is sensed through the integrated resistor  $R_{SENSE}$  and the voltage is applied to the non inverting input of the PWM comparator, see [Figure 2 on page 3](#). As soon as the sensed voltage is equal to the voltage derived from the COMP pin, the power MOSFET is switched OFF.

In parallel with the PWM operations, the comparator OCP, see [Figure 2 on page 3](#), checks the level of the drain current and switch OFF the power MOSFET in case the current is higher than the threshold  $I_{Dlim}$ , see [Table 8 on page 7](#).

The level of the drain current limit,  $I_{Dlim}$ , can be reduced depending from the sunk current from the pin LIM. The resistor  $R_{LIM}$ , between LIM and GND pins, fixes the current sunk and than the level of the current limit,  $I_{Dlim}$ , see [Figure 13 on page 9](#).

When the LIM pin is left open or if the  $R_{LIM}$  has an high value (i.e.  $> 80\text{ k}\Omega$ ) the current limit is fixed to its default value,  $I_{Dlim}$ , as reported on [Table 8 on page 7](#).

## 12 FB pin and COMP pin

The device can be used both in non-isolated and in isolated topology. In case of non-isolated topology, the feedback signal from the output voltage is applied directly to the FB pin as inverting input of the internal error amplifier having the reference voltage,  $V_{REF\_FB}$ , see the [Table 8 on page 7](#).

The output of the error amplifier sources and sinks the current,  $I_{COMP}$  respectively to and from the compensation network connected on the COMP pin. This signal is then compared, in the PWM comparator, with the signal coming from the SenseFET; the power MOSFET is switched off when the two values are the same on cycle by cycle basis. See the [Figure 2 on page 3](#) and the [Figure 22 on page 15](#).

When the power supply output voltage is equal to the error amplifier reference voltage,  $V_{REF\_FB}$ , a single resistor has to be connected from the output to the FB pin. For higher output voltages the external resistor divider is needed. If the voltage on FB pin is accidentally left floating, an internal pull-up protects the controller.

The output of the error amplifier is externally accessible through the COMP pin and it's used for the loop compensation: usually an RC network.

As reported on [Figure 22 on page 15](#), in case of isolated power supply, the internal error amplifier has to be disabled (FB pin shorted to GND). In this case an internal resistor is connected between an internal reference voltage and the COMP pin, see the [Figure 22 on page 15](#). The current loop has to be closed on the COMP pin through the opto-transistor in parallel with the compensation network. The  $V_{COMP}$  dynamics ranges is between  $V_{COMPL}$  and  $V_{COMP_H}$  as reported on [Figure 23 on page 16](#).

When the voltage  $V_{COMP}$  drops below the voltage threshold  $V_{COMPL}$ , the converter enters burst mode, see [Section 13 on page 16](#).

When the voltage  $V_{COMP}$  rises above the  $V_{COMPH}$  threshold, the peak drain current will reach its limit, as well as the deliverable output power.

**Figure 22. Feedback circuit**

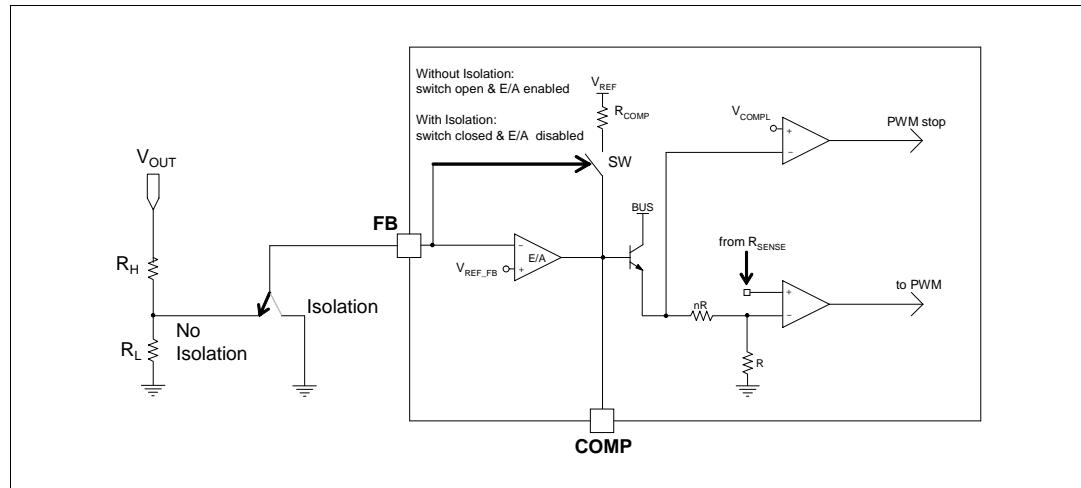
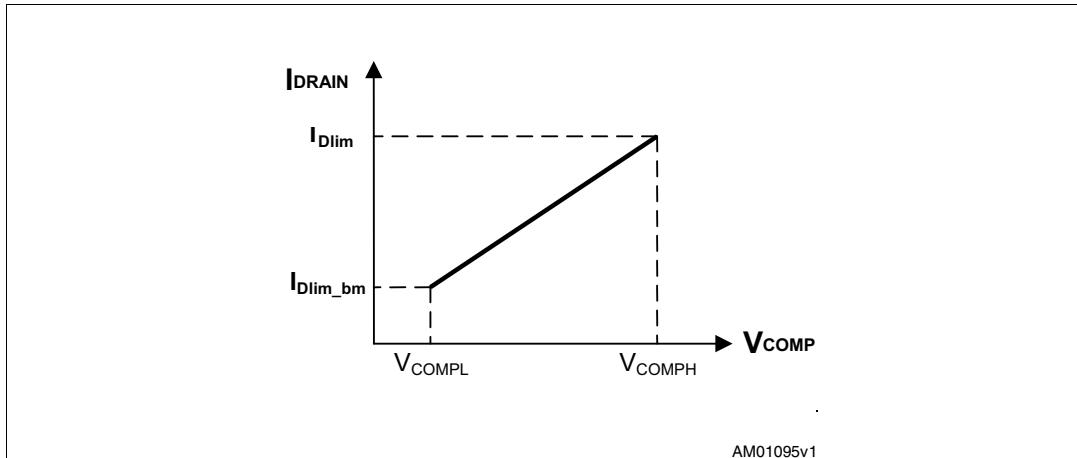
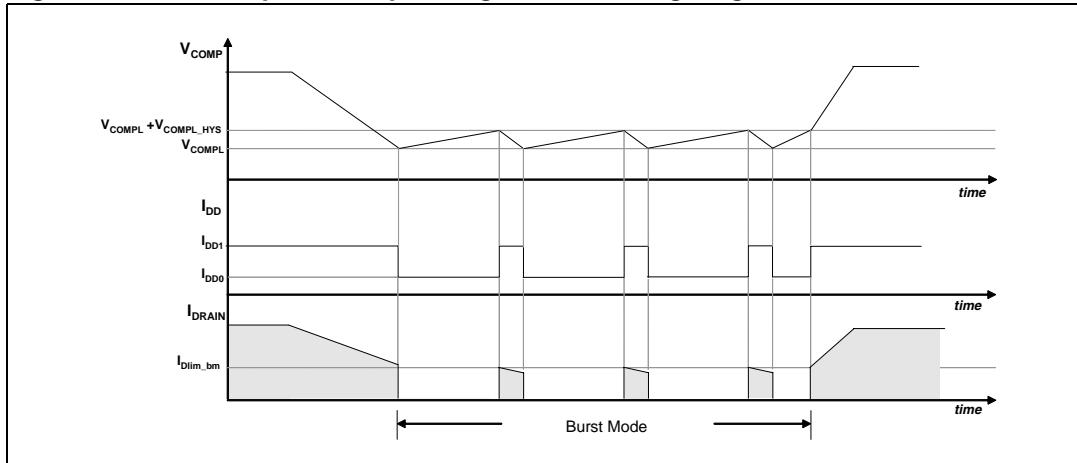


Figure 23. COMP pin voltage versus  $I_{DRAIN}$ 

## 13 Burst mode

When the voltage  $V_{COMP}$  drops below the threshold,  $V_{COMPL}$ , the power MOSFET is kept in OFF state and the consumption is reduced to  $I_{DD0}$  current, as reported on [Table 7 on page 6](#). As reaction at the energy delivery stop, the  $V_{COMP}$  voltage increases and as soon as it exceeds the threshold  $V_{COMPL} + V_{COMPL\_HYS}$ , the converter starts switching again with consumption level equal to  $I_{DD1}$  current. This ON-OFF operation mode, referred to as “burst mode” and reported on [Figure 24 on page 16](#), reduces the average frequency, which can go down even to a few hundreds hertz, thus minimizing all frequency-related losses and making it easier to comply with energy saving regulations. During the burst mode, the drain current limit is reduced to the value  $I_{Dlim\_bm}$  (reported on [Table 8 on page 7](#)) in order to avoid the audible noise issue.

Figure 24. Load-dependent operating modes: timing diagrams

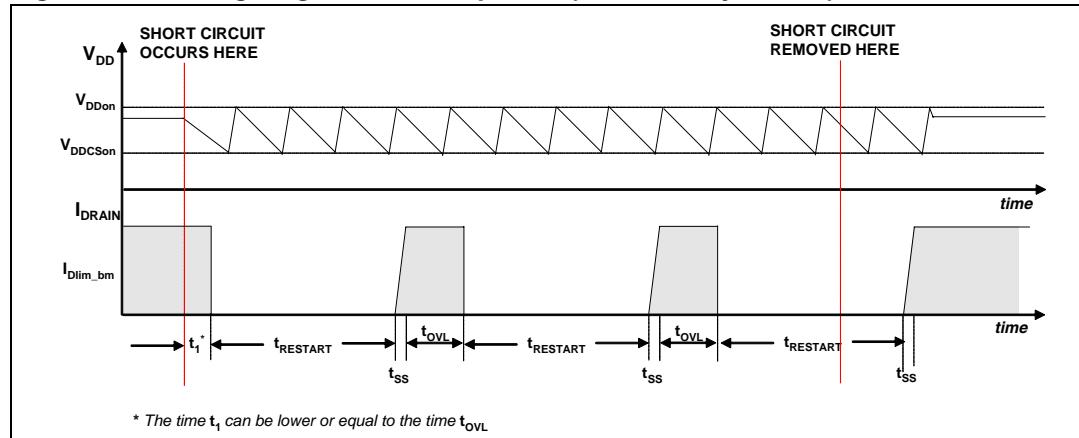


## 14 Automatic auto restart after overload or short-circuit

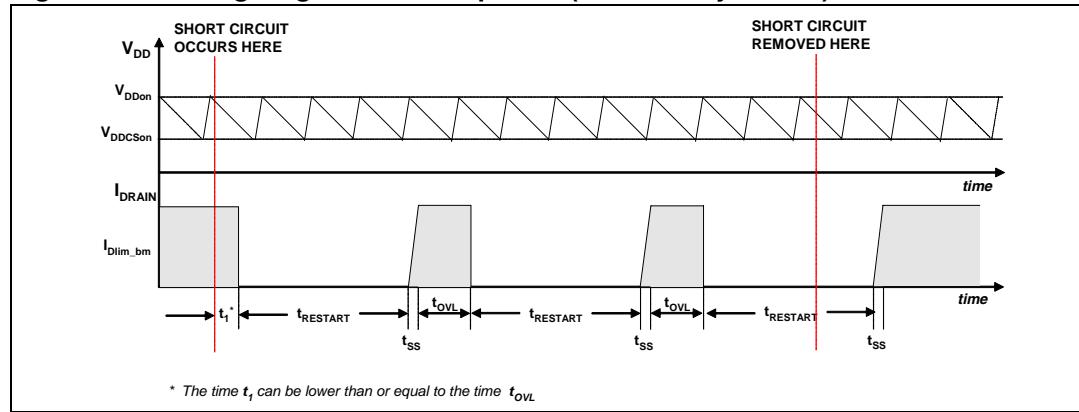
The overload protection is implemented in automatic way using the integrated up-down counter. Every cycle, it is incremented or decremented depending if the current logic detects the limit condition or not. The limit condition is the peak drain current,  $I_{Dlim}$ , reported on [Table 8 on page 7](#) or the one set by the user through the  $R_{LIM}$  resistor, as reported in [Figure 13 on page 9](#). After the reset of the counter, if the peak drain current is continuously equal to the level  $I_{Dlim}$ , the counter will be incremented till the fixed time,  $t_{OVL}$ , after that will be disabled the power MOSFET switch ON. It will be activated again, through the soft start, after the  $t_{RESTART}$  time, see the [Figure 25](#) and [Figure 26 on page 17](#) and the mentioned time values on [Table 8 on page 7](#).

In case of overload or short-circuit event, the power MOSFET switching will be stopped after a time that depends from the counter and that can be as maximum equal to  $t_{OVL}$ . The protection will occur in the same way until the overload condition is removed, see [Figure 25](#) and [Figure 26 on page 17](#). This protection ensures restart attempts of the converter with low repetition rate, so that it works safely with extremely low power throughput and avoiding the IC overheating in case of repeated overload events. If the overload is removed before the protection tripping, the counter will be decremented cycle by cycle down to zero and the IC will not be stopped.

**Figure 25. Timing diagram: OLP sequence (IC externally biased)**



**Figure 26. Timing diagram: OLP sequence (IC internally biased)**



## 15 Open loop failure protection

In case the power supply is built in fly-back topology and the VIPer16 is supplied by an auxiliary winding, as shown in [Figure 27 on page 18](#) and [Figure 28 on page 19](#), the converter is protected against feedback loop failure or accidental disconnections of the winding.

The following description is applicable for the schematics of [Figure 27 on page 18](#) and [Figure 28 on page 19](#), respectively the non-isolated fly-back and the isolated fly-back.

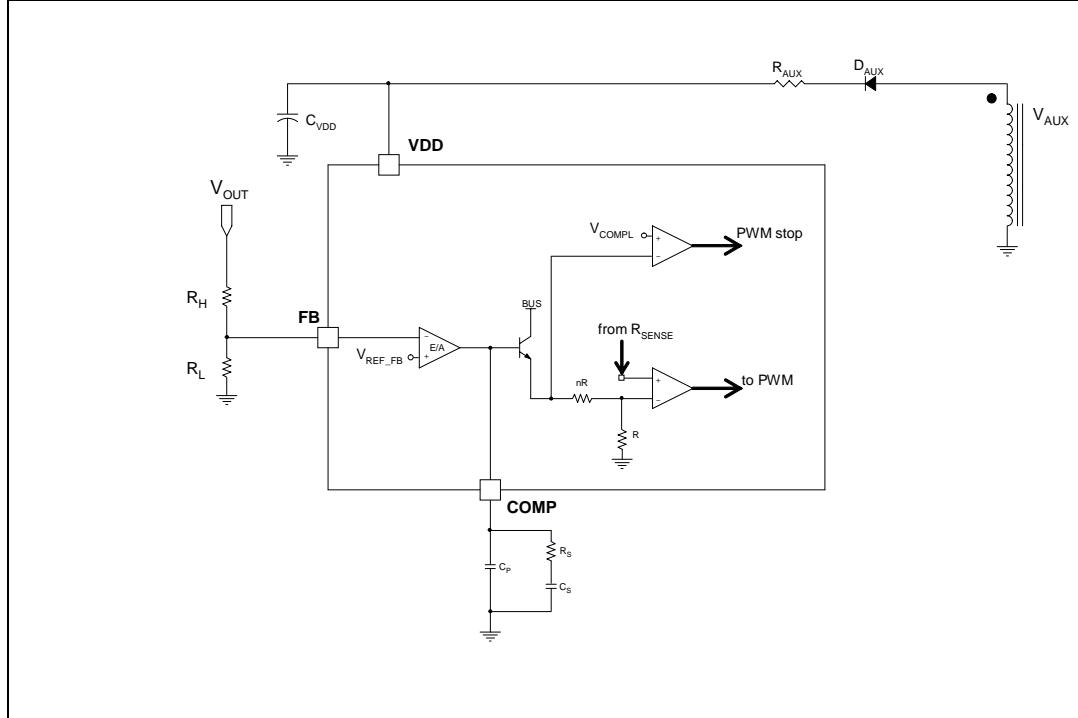
If  $R_H$  is opened or  $R_L$  is shorted, the VIPer16 works at its drain current limitation. The output voltage,  $V_{OUT}$ , will increase and so the auxiliary voltage,  $V_{AUX}$ , which is coupled with the output through the secondary-to-auxiliary turns ratio.

As the auxiliary voltage increases up to the internal  $V_{DD}$  active clamp,  $V_{DD\text{clamp}}$  (the value is reported on [Table 8 on page 7](#)) and the clamp current injected on VDD pin exceeds the latch threshold,  $I_{DD\text{ol}}$  (the value is reported on [Table 8 on page 7](#)), a fault signal is internally generated.

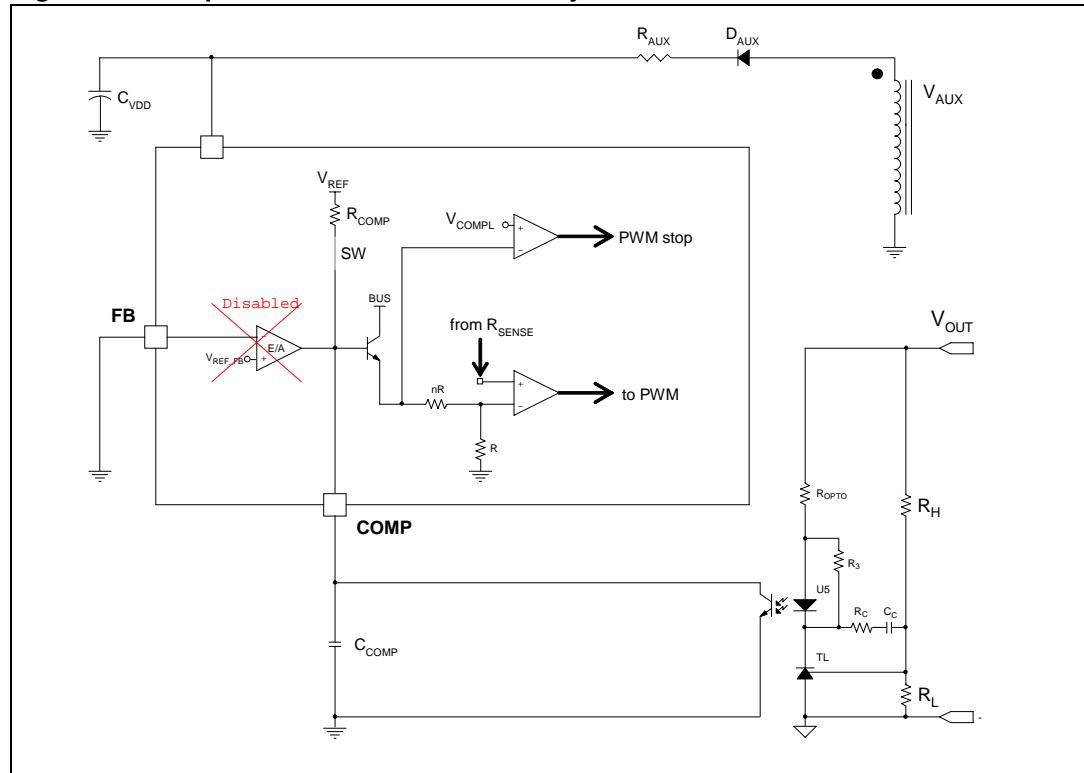
In order to distinguish an actual malfunction from a bad auxiliary winding design, both the above conditions (drain current equal to the drain current limitation and current higher than  $I_{DD\text{ol}}$  through VDD clamp) have to be verified to reveal the fault.

If  $R_L$  is opened or  $R_H$  is shorted, the output voltage,  $V_{OUT}$ , will be clamped to the reference voltage  $V_{REF\_FB}$  (in case of non isolated fly-back) or to the external TL voltage reference (in case of isolated fly-back).

**Figure 27. FB pin connection for non-isolated fly-back**



**Figure 28. FB pin connection for isolated fly-back**



## 16 Package mechanical data

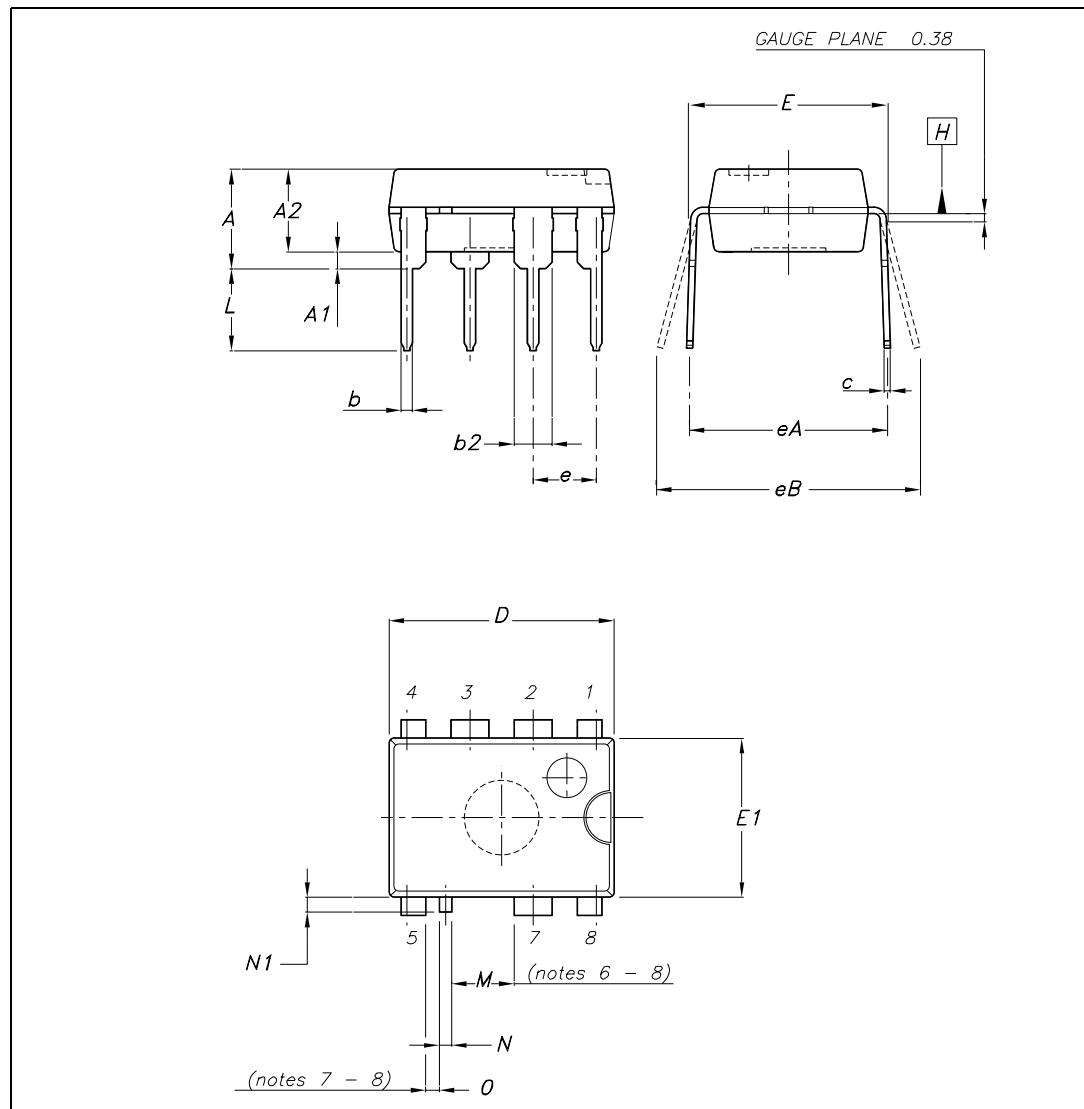
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**Table 9. DIP-7 mechanical data**

Dim.	mm		
	Typ	Min	Max
A			5,33
A1		0,38	
A2	3,30	2,92	4,95
b	0,46	0,36	0,56
b2	1,52	1,14	1,78
c	0,25	0,20	0,36
D	9,27	9,02	10,16
E	7,87	7,62	8,26
E1	6,35	6,10	7,11
e	2,54		
eA	7,62		
eB			10,92
L	3,30	2,92	3,81
M <sup>(6)(8)</sup>	2,508		
N	0,50	0,40	0,60
N1			0,60
O <sup>(7)(8)</sup>	0,548		

- 1- The leads size is comprehensive of the thickness of the leads finishing material.
- 2- Dimensions do not include mold protrusion, not to exceed 0,25 mm in total (both side).
- 3- Package outline exclusive of metal burrs dimensions.
- 4- Datum plane "H" coincident with the bottom of lead, where lead exits body.
- 5- Ref. POA MOTHER doc. 0037880
- 6- Creepage distance > 800 V
- 7- Creepage distance 250 V
- 8- Creepage distance as shown in the 664-1 CEI / IEC standard.

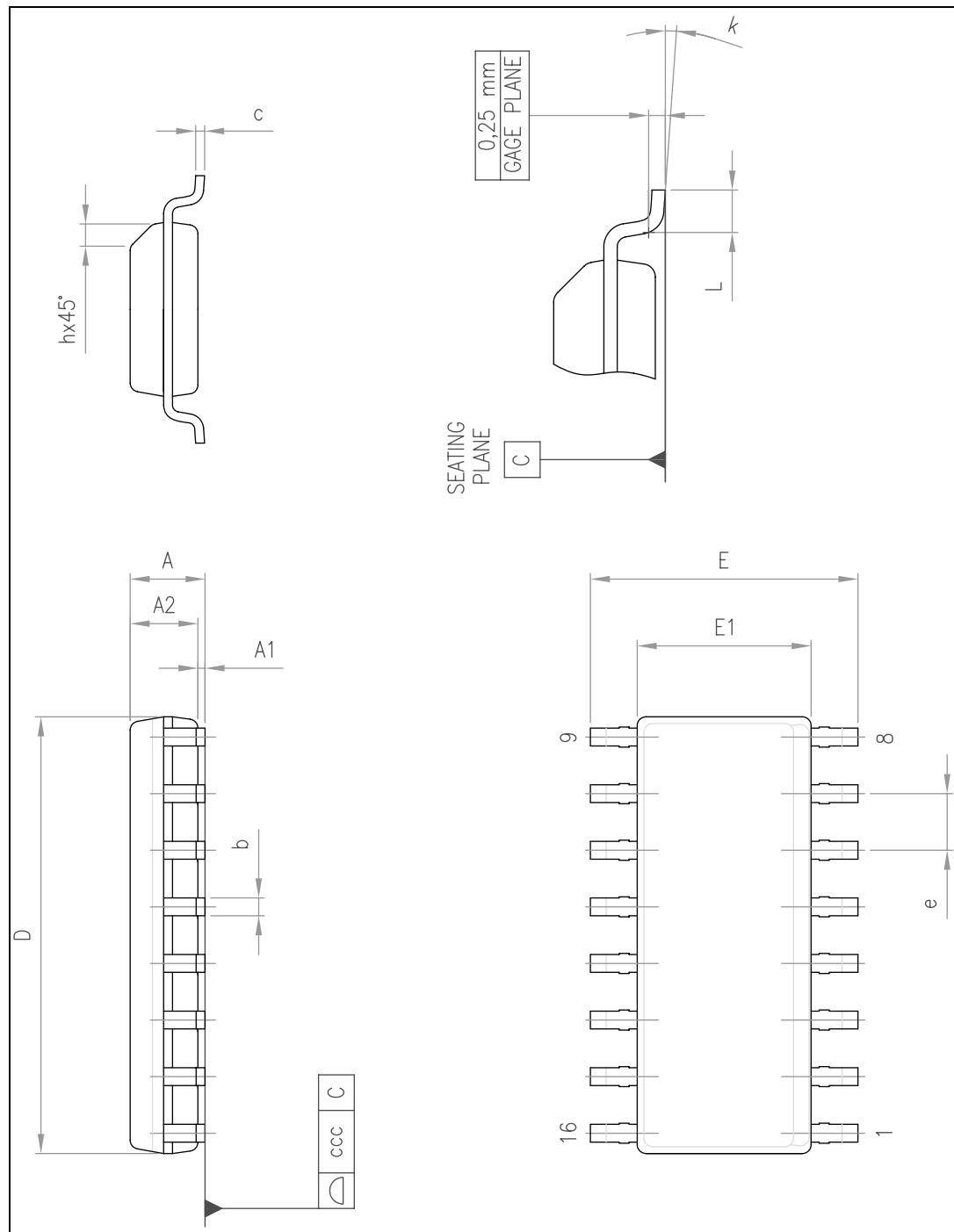
Figure 29. DIP-7 package dimensions



**Table 10. SO16N mechanical data**

Dim.	mm		
	Min	Typ	Max
A			1.75
A1	0.1		0.25
A2	1.25		
b	0.31		0.51
c	0.17		0.25
D	9.8	9.9	10
E	5.8	6	6.2
E1	3.8	3.9	4
e		1.27	
h	0.25		0.5
L	0.4		1.27
k	0		8
ccc			0.1

Figure 30. SO16N Package dimensions



## 17 Revision history

**Table 11. Document revision history**

Date	Revision	Changes
21-Jan-2009	1	Initial release
07-Dec-2009	2	Updated <a href="#">Figure 7 on page 8</a>
14-May-2010	3	Updated <a href="#">Figure 3 on page 4</a> and <a href="#">Table 3 on page 4</a>
26-Aug-2010	4	Updated <a href="#">Table 3 on page 4</a> , <a href="#">Figure 16 on page 10</a> and <a href="#">Figure 21 on page 13</a>
10-Oct-2011	5	Updated <a href="#">Figure 30 on page 23</a> and <a href="#">Table 7 on page 6</a>

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